We report on a metasurface laser emitting at the valley extremum of a multivalley energy-momentum dispersion. Such peculiar dispersion shape is obtained by hybridizing high quality factor photonic modes of different symmetry and opposite effective mass. The lasing effect takes place at high oblique angle ($\sim$20 degrees), in the telecom wavelength range ($\sim$1580 nm), on silicon substrate and operating at room temperature. Our results show the potential of multivalley dispersion for micro-laser in integrated photonic and beam-steering applications. It also opens the way to study various features of valleytronic physics such as spontaneous momentum symmetry breaking, two-mode squeezing and Josephson oscillation in momentum space.

Multivalley dispersion: The vertical symmetry breaking due to the presence of a “residual” slab [i.e. the unpatterned layer of thickness $h_2$ in Fig. 1(a)] makes
it possible to couple modes of opposite vertical symmetry, thus changes drastically the photonic dispersion from the one of symmetric design [30]. To obtain multivalley dispersion, we harness the hybridization between two TE-polarized modes $E_o$ of conventional parabolic dispersions with opposite curvature (i.e. photonic mass) [see Fig 1(b)]. Such coupling results in an anticrossing effect, corresponding to valley formation [point C and D in Fig 1(b)] in a W-shaped and M-shaped dispersion. The distribution of the electric field at different extrema of the dispersion diagram is discussed above were originally at the edge of the Brillouin zone ($k_x = \pm \frac{\pi}{a}$) and below the lightline of the monomer design (i.e. $\alpha = 0$). They were thus lossless and could not radiate to the free space. By implementing the double-period perturbation, we obtain an unit cell of period twice larger, thus a Brillouin zone twice smaller than the one of the monomer. The previous modes are then folded to $k_x = 0$ and start radiating to the free space. As consequence, the quality factor of the hybrid modes can be finely tuned by $\alpha$, following a very simple law: $Q \propto 1/\alpha^2$ [30]. To illustrate this effect, the quality factor at the extrema of Fig. 1(b) are extracted via numerical simulations and reported in the upper panel on Fig. 1(d). The simulations evidence the dependence in $1/\alpha^2$ of the quality factors. Moreover, the balance of radiative losses at the valley extrema are also verified, with $\frac{1}{Q_C} = \frac{1}{Q_A} = \frac{1}{2}(\frac{1}{Q_o} + \frac{1}{Q_e})$. Furthermore, as shown in the lower panel of Fig. 1(d), when modifying $\alpha$, the spectral position of extrema stay at the same values (for $\alpha < 0.1$). So the double period perturbation allows for a fine tuning of the quality factor while unchanging the farfield pattern of the metasurface. Finally, we note that $Q_C \approx 1.5Q_A$ for every values of $\alpha$, thus if a gain medium is inserted in the spectral range of the W-shaped dispersion, the lasing effect will be favoured to take place at the valley extremum (point C) instead at $k_x = 0$ (point A).

Based-on the dimer design discussed above, the structure of the fabricated sample is presented in Fig. 2(a). Scanning Electron Microscopy (SEM) images of the metasurface ($30 \times 30 \mu m^2$) are shown in Fig. 2(b). The unpatterned slab (i.e. “residual” layer to break the vertical symmetry of the design) consists of an InP layer which was growth by Molecular Beam Epitaxy (MBE) on sacrificial buffer, then transfered by molecular bonding to...
2 µm of SiO₂ on Silicon substrate. As active materials, four InAsP quantum wells are embedded within the InP layer during the MBE growth. The patterned layer of dimerized lattice is made from amorphous silicon. This layer was first deposited by Plasma-Enhanced Chemical Vapor Deposition (PECVD) deposition. Then the patterning was performed via electronic beam lithography and plasma-assisted dry etching. In the same notations as the design in Fig 1(a), the geometrical parameters of the fabricated sample are: \( h_1 = 250 \) nm, \( h_2 = 245 \) nm, \( a = 189 \) nm, \( b = 171 \) nm and \( \alpha = 0.1 \).

![FIG. 2. (a) Sketch of the unit cell of the fabricated sample. (b) SEM images of the metasurface structure on the fabricated sample.](image)

Angle-resolved photoluminescence experiment is performed to obtain the energy-momentum dispersion of the fabricated metasurface. The experimental setup is shown in Fig. 3(a). The excitation source is a 980 nm laser which can be used in two modes: continuous-wave (cw) or picosecond pulsed (pulse width of 50ps, repetition rate of 80 Mhz). The excitation laser is focused onto the metasurface via a microscope objective (x50, NA=0.42), forming a spot-size of \( 2 \) – \( 3 \) µm. Photoluminescence of InAsP quantum wells are collected via the same objective and projected onto the entrance slit of a spectrometer. The sample orientation is aligned so that the corrugated direction (i.e. x-axis) is along the entrance slit. A set of lenses are carefully used so that the projection of the photoluminescence image is in the Fourier space (i.e. \( k_x \) and \( k_y \)). The output of the spectrometer is coupled to a CMOS sensor of InAs array (640x512). Thus the image obtained from the camera give us directly the energy-momentum dispersion diagram along \( k_x \). A multivalley dispersion of W-shaped is clearly evidenced when pumping the metasurface by cw excitation [see fig. 3(a)]. The experimental dispersion is perfectly reproduced by numerical simulations and also well fitted by the analytical coupled-mode theory presented previously. We note that the measured mode is much broader than the theoretical prediction (\( Q_{\text{theory}} = 2100 \) at the valley minimum) due to the absorption of the quantum wells.

To study the lasing effect, photoluminescence experiment at different pumping power of pulsed excitation has been performed. Figure. 4(a) reports the integrated intensity as a function of excitation power, showing clearly a lasing effect with pumping threshold of \( p_{\text{thres}} \approx 10 \) µW, measured at the output of microscope objective. This average power corresponds to a pumping fluence of \( 2.5 \) µJ/cm². Angle-resolved photoluminescence is monitored when increase the pumping power from below threshold [i.e. \( 0.8 p_{\text{thres}} \), see Fig. 4(b)] to above threshold [i.e. \( 1.3 p_{\text{thres}} \), see Fig. 4(c)]. Below threshold, similar to the case of cw pumping, the spontaneous emission of InAsP quantum wells “populates” the whole dispersion branch, leading to a very broadband emission of more than 200 nm. Most interestingly, above threshold, we clearly observe the stimulation of emission to the valley point of W-shaped dispersion (\( k_L = 1.31 \) µm\(^{-1} \)). This lasing effect is associated to an emission at 1581 nm (i.e. 784 meV), emitting along a very high oblique angle \( \theta_L = 19.1 \), and within a sharp linewidth 0.8 nm (i.e. 0.4 meV at 1.3\( p_{\text{thres}} \)) when compared to the one of spontaneous emission [see Fig. 4(d)]. Although the quality factor estimated from the lasing linewidth is as high as \( Q_{\text{lasing}} = 1975 \) and very close to the one theoretically predicted (\( Q_{\text{theory}} = 2100 \)), this value is in fact limited by dephasing processus in the system, thus not representative to the real quality factor of our photonic mode. The correct method to estimate the quality factor is to extract the linewidth when the pumping power is slightly bellow threshold. Indeed, this
pumping condition corresponds approximatively to the transparency regime of the gain material, in which there is no more broadening due to quantum well absorption. Figure 4(e) depicts the emission spectrum at $\theta_L$ when pumping at 0.95 $P_{\text{thres}}$. From the extracted linewidth (0.8 meV), we estimate a quality factor of $Q = 974$. The fact that this experimental value is inferior than the one of the theoretical prediction is likely due to the fabrication imperfection. Finally, to characterize the directivity of our lasing emission, the emission intensity as a function of the in-plan wavevector, when pumping above threshold, is reported in Fig. 4(f). By fitting the experimental data with a Gaussian distribution, we extract an emission directivity within $\Delta k = 0.43 \mu m^{-1}$. This value is in good agreement ($\Delta k, \Delta x \approx 1$) with the size of the cavity effect induced by the pump of a 2–3 $\mu m$ spot-size.

We highlight that the conception of our metasurface makes it possible to tailor separately the dispersion shape and the quality factor, thus suggests a unique scheme to obtain simultaneously valley extrema at high momentum and high quality factor. Such scenario leads to the possibility of directional lasing at arbitrary angle with very low threshold power. As matter of fact, for the same angle range, the threshold of our directional laser is one order of magnitude lower than one reported in the literature [29] which requires a trade-off between emission angle and quality factor.

Furthermore, it is possible to extend the photonic concept of our metasurface to polaritonic physics when light-matter interaction takes place in the strong coupling regime [32]. This will be achieved by either working at cryogenic temperature or with quantum wells of high-binding energy excitons (GaN, ZnO, transition metal dichalcogenides and perovskites) [33]. As a matter of fact, the multivalley dispersion and valley lasing demonstrated in this work are the most important building blocks to study polariton valleytronic physics [34, 35]. Indeed, it has been recently predicted that strong cou-
pling regime with W-shaped dispersion would lead to Bose Einstein condensation at the valley extrema. The formation of such macroscopic bosonic states at the valley extrema will pave the way to study spontaneous symmetry breaking, two-mode squeezing and Josephson oscillation in momentum space.

In conclusion, by engineering multivalley dispersion of high quality factor, we have demonstrated experimentally a metasurface laser which emits coherent light of telecom wavelength along high oblique angle, on silicon substrate and operating at room temperature. The design of our devices provides a high degree of freedom for choosing the lasing direction and the quality factor of the photonic mode, thus very promising for integrated beam steering system of LIDAR and LIFI applications. Moreover, our design can be easily extended to other material family, and perfectly adapted for operation in the strong coupling regime of light-matter interaction for studying the valleytronics physics of Bose Einstein condensation.

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